

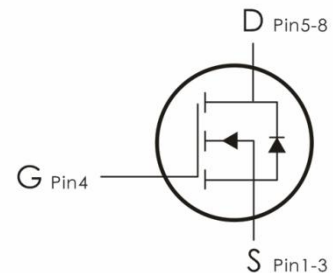
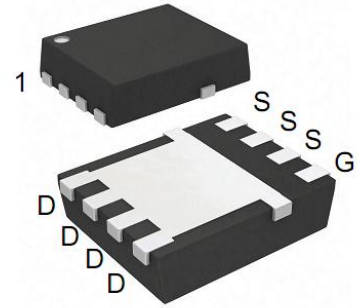
Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-30V, I_D=-60A, R_{DS(ON)}<7\text{ m}\Omega @V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DON60P03	60P03	DFN5*6-8	5000 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	-60	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$	-44	
I_{DM}	Pulsed Drain Current ¹	-240	
P_D	Power Dissipation	75	W
E_{AS}	Single pulse avalanche energy	289	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.67	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	-30	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-30V	---	---	-1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	±100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	-1	-1.6	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance	V _{GS} =-10V, I _D =-20A	---	5.7	7	m Ω
		V _{GS} =-4.5V, I _D =-20A	---	8	10.5	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	3150	---	pF
C _{oss}	Output Capacitance		---	358	--	
C _{rss}	Reverse Transfer Capacitance		---	342	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =-15V, I _D =-20A, R _L =3 Ω ,V _{GS} =-10V	---	10	---	ns
t _r	Rise Time		---	47	---	ns
t _{d(off)}	Turn-Off Delay Time		---	75	---	ns
t _f	Fall Time		---	44	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-20A	---	13	---	nc
Q _{gs}	Gate-Source Charge		---	15	---	nc
Q _{gd}	Gate-Drain “Miller” Charge		---	5	---	nc
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage ¹	V _{GS} =0V, I _{SD} =-20A	---	---	-1.2	V
I _S	Continuous Drain Curren ³	V _D =V _G =0V	---	---	-60	A
I _{SM}	Pulsed Drain Current		---	---	-240	A

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=-30V$, $V_G=-10V$, $R_G=25\Omega$, $L=0.5mH$.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

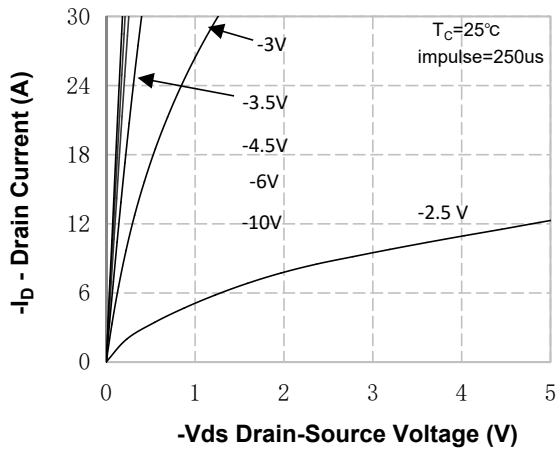


Figure 1. On-Region Characteristics

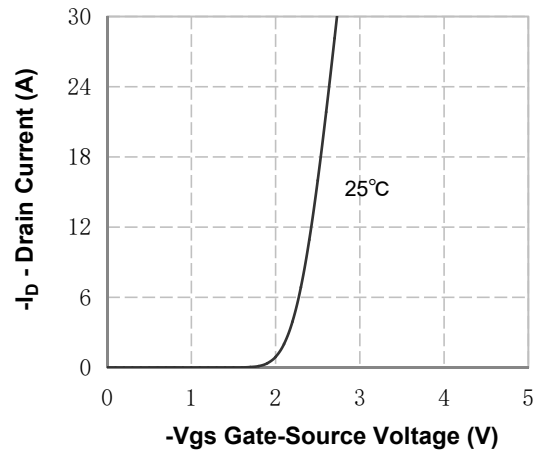


Figure 2. Transfer Characteristics

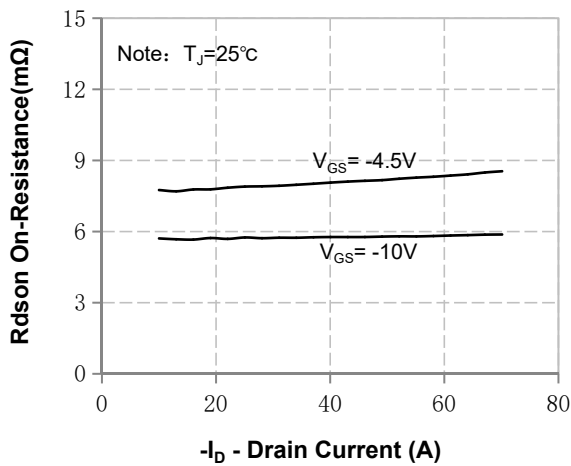


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

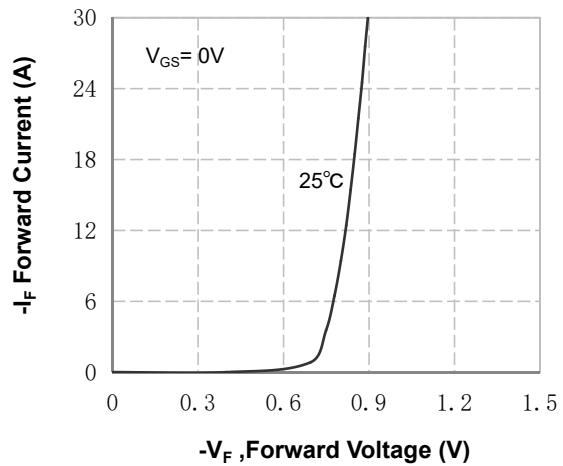


Figure 4. Body Diode Forward Voltage Variation with Source Current

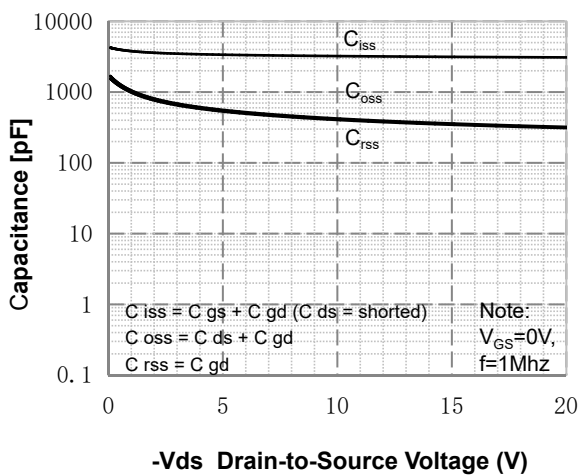


Figure 5. Capacitance Characteristics

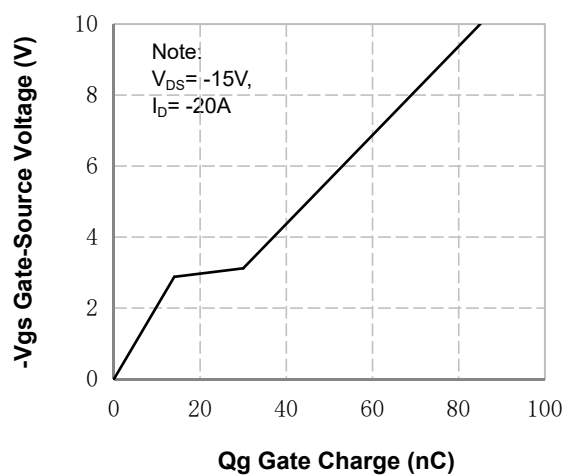


Figure 6. Gate Charge Characteristics

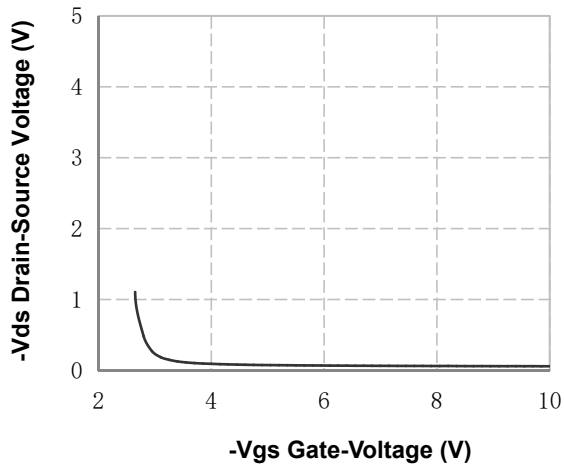


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

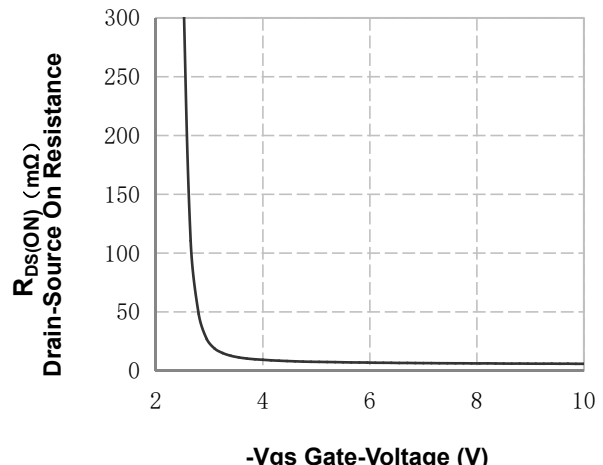


Figure 8. On-Resistance vs Gate Voltage

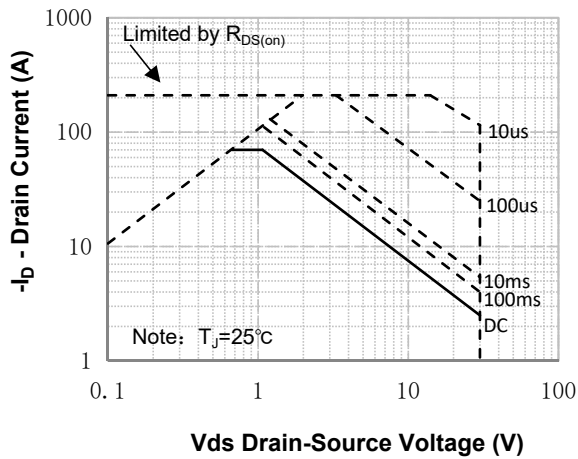


Figure 9. Maximum Safe Operating Area

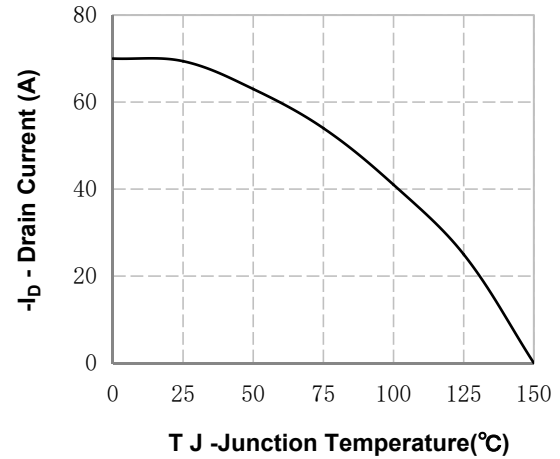


Figure 10. Maximum Continuous Drain Current vs Case Temperature

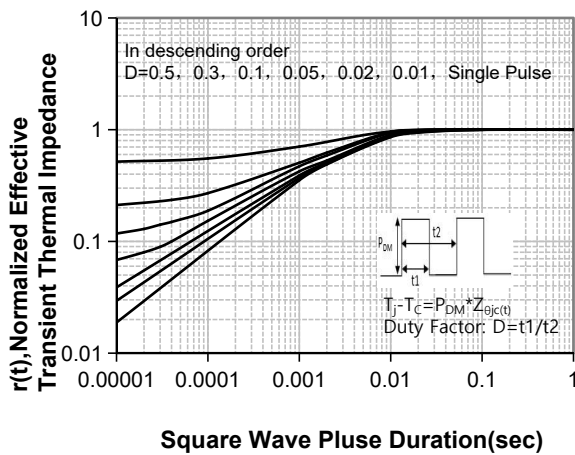
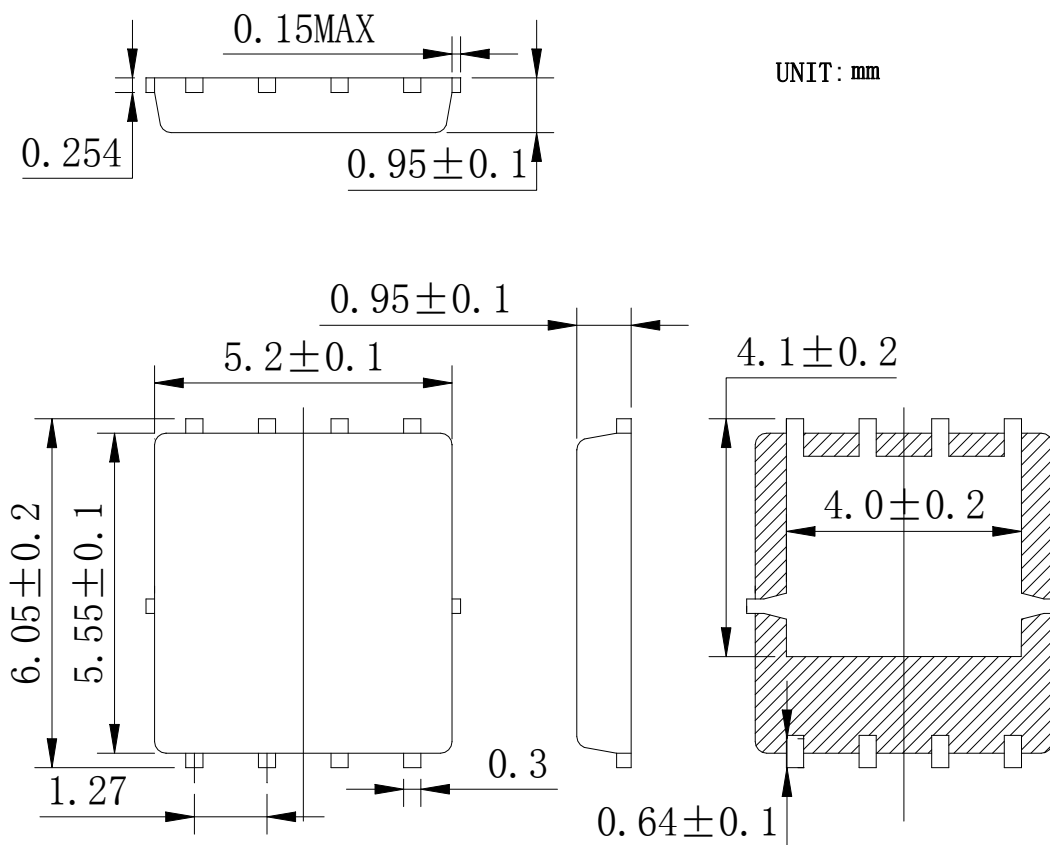


Figure 11. Transient Thermal Response Curve

DFN5x6-8 Package Information:



Marking Information:

①. Doingter LOGO

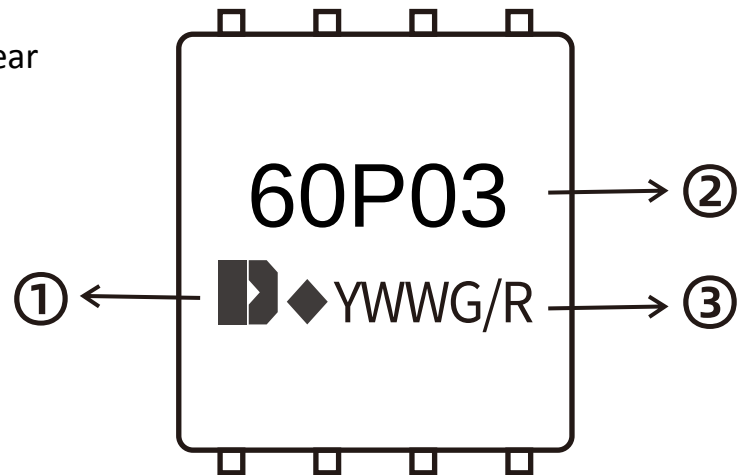
②. Part NO.

③. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2024-06-28	Release of final version

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